

View Online at <https://aerobasegroup.com/nsn/5961-01-624-7502>

Inclosure Material:

Glass and metal

Overall Length:

Between 1.335 inches and 1.345 inches

Overall Height:

Between 0.147 inches and 0.200 inches

Overall Width:

Between 0.535 inches and 0.545 inches

Function For Which Designed:

Programmable transistor

Internal Configuration:

Field effect

Electrode Internally-electrically Connected To Case:

Gate

Internal Junction Configuration:

Npn

Voltage Rating In Volts Per Characteristic:

-0.5 drain to source voltage and 65.0 drain to source voltage

Current Rating Per Characteristic:

10.0 microamperes zero-gate-voltage drain current

Power Rating Per Characteristic:

90.0 watts cw power

Maximum Operating Temperature Per Measurement Point:

150.0 degrees celsius case and 200.0 degrees celsius junction

Product Name:

Rf power field effect transistor

Special Features:

Tech data shows this item was no longer manufactured since 2010; in tape and reel, r3 suffix =250 units per 56mm, 13 inch reel; rohs compliant; designed for gsm and gsm edge base station applications with frequencies from 1800 to 2000 mhz; designed for maximum gain and insertion phase flatness; suitable for fm, tdma, cdma and multicarrier amplifier applications; to be used in class ab for gsm and gsm edge cellular radio applications; integrated esd protections; high efficiency; high linearity

Terminal Type And Quantity:

3 pin

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0